

20V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

V_{(BR)DSS}= 20V : R_{DS}(_{on})=0.06Ω; I_D= 4.1A

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

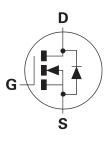
DEVICE	REEL	TAPE	QUANTITY
	SIZE	WIDTH	PER REEL
ZXMN2A14FTA	7″	8mm	3000 units

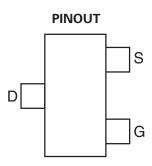
DEVICE MARKING

• 214

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SOT23







ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current @ V_{GS} =4.5V; T _A =25°C ^(b)	I _D	4.1	А
@ $V_{GS}=4.5V$; $T_A=70^{\circ}C$ ^(b) @ $V_{GS}=4.5V$; $T_A=25^{\circ}C$ ^(a)		3.3	А
@ V_{GS} =4.5V; T_{A} =25°C ^(a)		3.4	А
Pulsed Drain Current ^(c)	I _{DM}	19	A
Continuous Source Current (Body Diode) ^(b)	I _S	1.7	A
Pulsed Source Current (Body Diode) ^(c)	I _{SM}	19	A
Power Dissipation at $T_A = 25^{\circ}C^{(a)}$	P _D	1	W
Linear Derating Factor		8	mW/°C
Power Dissipation at T _A =25°C ^(b)	P _D	1.5	W
Linear Derating Factor		12	mW/°C
Operating and Storage Temperature Range	T _j , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

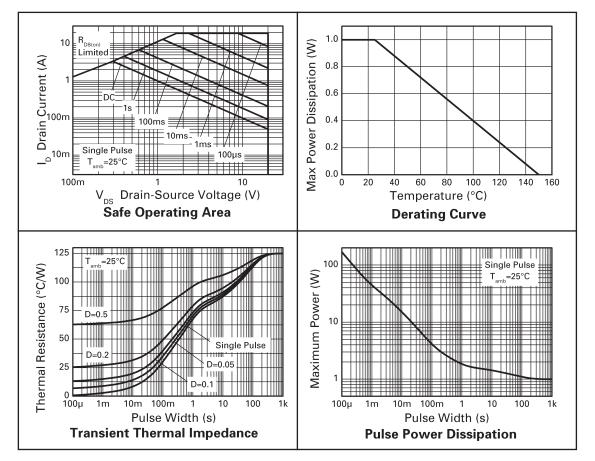
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\Theta JA}$	125	°C/W
Junction to Ambient ^(b)	$R_{\Theta JA}$	82	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. (b) For a device surface mounted on FR4 PCB measured at t \leq 5 sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300 µs - pulse width limited by maximum junction temperature.





CHARACTERISTICS



PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC	•					
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =20V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	$V_{GS}=\pm 12V, V_{DS}=0V$
Gate-Source Threshold Voltage	V _{GS(th)}	0.7			V	$I_{D} = 250 \mu A, V_{DS} = V_{GS}$
Static Drain-Source On-State	R _{DS(on)}			0.060	Ω	V _{GS} =4.5V, I _D =3.4A
Resistance ⁽¹⁾				0.110	Ω	V _{GS} =2.5V, I _D =2.5A
Forward Transconductance ^{(1) (3)}	g _{fs}		9.4		S	V _{DS} =10V,I _D =3.4A
DYNAMIC ⁽³⁾						·
Input Capacitance	Ciss		544		pF	
Output Capacitance	C _{oss}		132		pF	V _{DS} = 10V, V _{GS} =0V,
Reverse Transfer Capacitance	C _{rss}		85		pF	f=1MHz
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		4.0		ns	
Rise Time	t _r		5.3		ns	V _{DD} = 10V, V _{GS} = 4.5V
Turn-Off Delay Time	t _{d(off)}		16.6		ns	$I_{D} = 1A$
Fall Time	t _f		9.5		ns	$R_{G} \cong 6.0\Omega$
Total Gate Charge	Qg		6.6		nC	
Gate-Source Charge	Q _{gs}		1.2		nC	V _{DS} =10V,V _{GS} = 4.5V,
Gate-Drain Charge	Q _{gd}		2.1		nC	I _D =3.4A
SOURCE-DRAIN DIODE	1	1	1			1
Diode Forward Voltage ⁽¹⁾	V _{SD}		0.85	0.95	V	T _J =25°C, I _S =(3.3)A,
						V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		11.4		ns	T _J =25°C, I _F =(1.7)A,

NOTES

Reverse Recovery Charge ⁽³⁾

(1) Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle ${\leq}2\%.$

(2) Switching characteristics are independent of operating junction temperature.

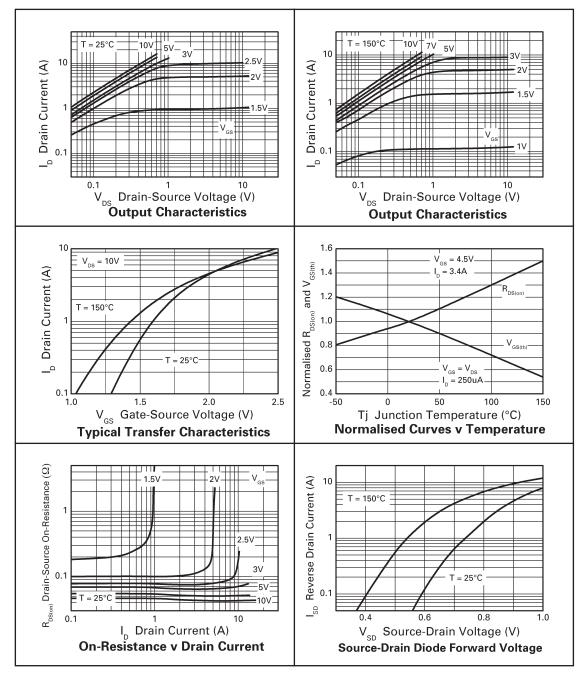
Q_{rr}

4.6

(3) For design aid only, not subject to production testing.

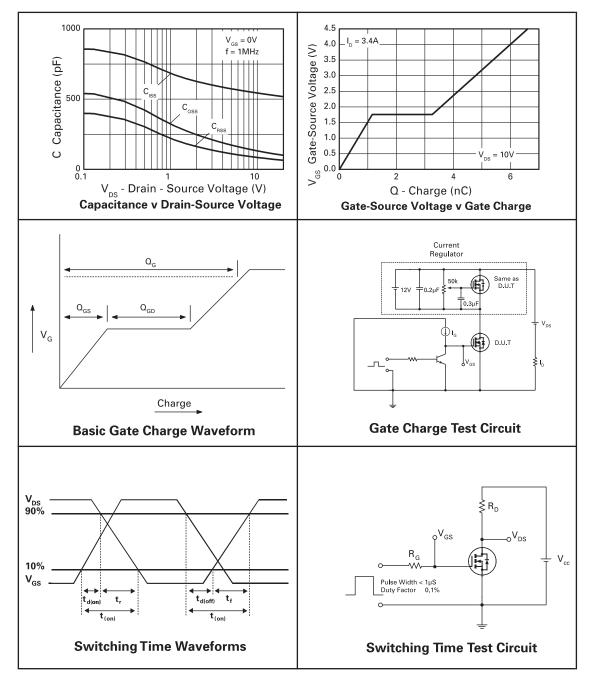


nC di/dt= 100A/µs



TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS



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"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

"Draft version"This term denotes a very early datasheet version and contains highly provisional

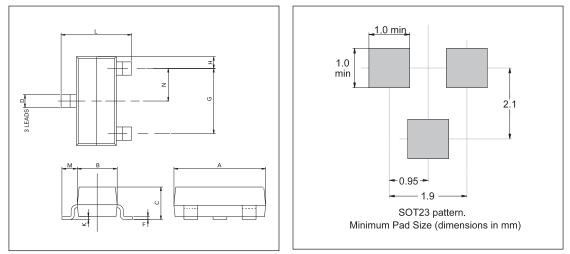
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PACKAGE OUTLINE



PAD LAYOUT

Controlling dimensions are in millimetres. Approximate conversions are given in inches

PACKAGE DIMENSIONS

	MILLIN	IETRES	INC	HES		MILLIMETRES		INCHES	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
Α	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	К	0.01	0.10	0.0004	0.004
С	_	1.10	_	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	Μ	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	Ν	0.95	NOM	0.0375	5 NOM
G	1.90	NOM	0.075	NOM	θ	10°	ТҮР	10°	ТҮР

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